

## P-Channel 1.8 V (G-S) MOSFET

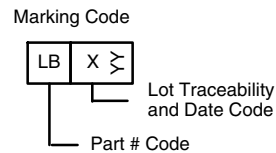
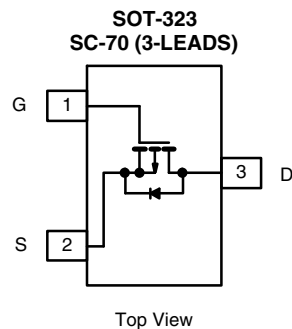
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
- 8	0.280 at V <sub>GS</sub> = - 4.5 V	- 0.92
	0.380 at V <sub>GS</sub> = - 2.5 V	- 0.79
	0.530 at V <sub>GS</sub> = - 1.8 V	- 0.67

### FEATURES

- TrenchFET® Power MOSFET: 1.8 V
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



**Ordering Information:** Si1305DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 8		V
Gate-Source Voltage	V <sub>GS</sub>	± 8		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	- 0.92	- 0.86
		T <sub>A</sub> = 70 °C	- 0.74	- 0.69
Pulsed Drain Current	I <sub>DM</sub>	- 3		A
Continuous Diode Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	- 0.28	- 0.24	
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	0.34	0.29
		T <sub>A</sub> = 70 °C	0.22	0.19
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 5 s	315	375
		Steady State	360	430
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	285	340	°C/W

Note:

a. Surface mounted on 1" x 1" FR4 board.

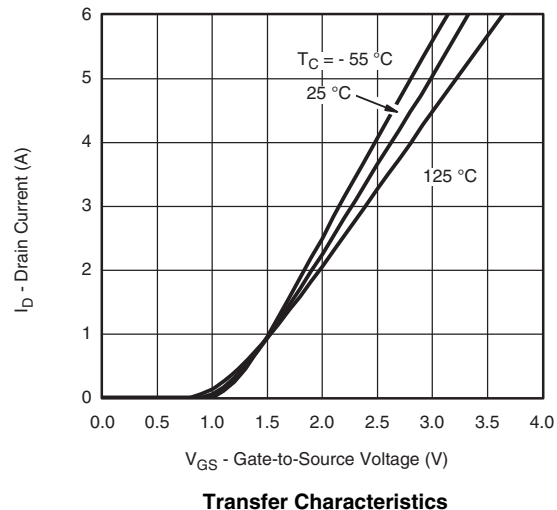
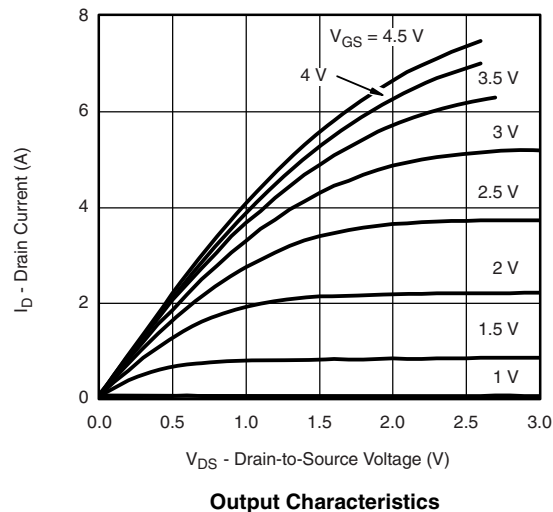
**SPECIFICATIONS** ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.45			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-3			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		0.230	0.280	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -0.5\text{ A}$		0.315	0.380	
		$V_{GS} = -1.8\text{ V}, I_D = -0.3\text{ A}$		0.440	0.530	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -1\text{ A}$		3.5		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -0.3\text{ A}, V_{GS} = 0\text{ V}$			-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		2.6	4	nC
Gate-Source Charge	$Q_{gs}$			0.6		
Gate-Drain Charge	$Q_{gd}$			0.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		8	15	ns
Rise Time	$t_r$			55	80	
Turn-Off Delay Time	$t_{d(off)}$			17	25	
Fall Time	$t_f$			12	20	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = -1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		27	

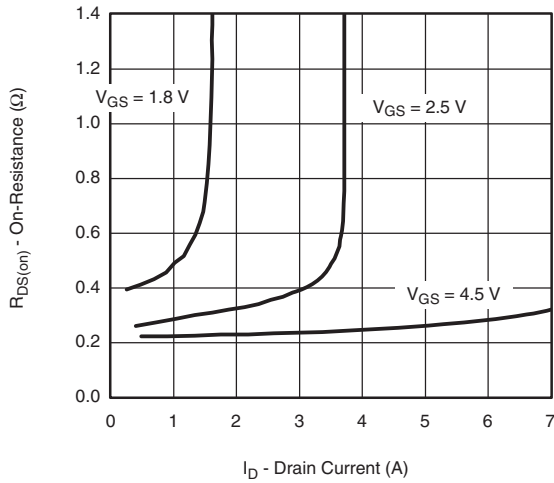
## Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

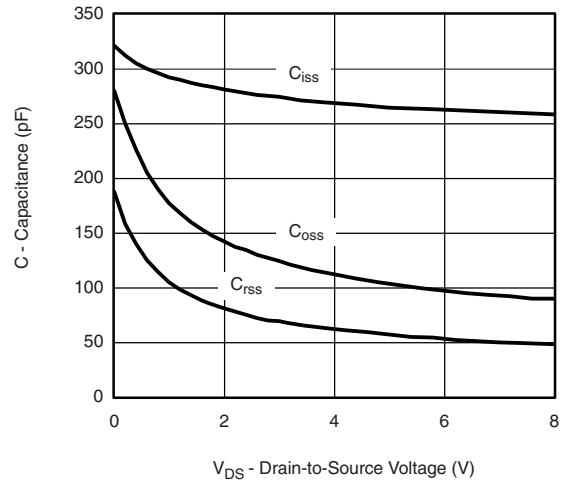
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $25\text{ }^\circ\text{C}$ , unless otherwise noted)

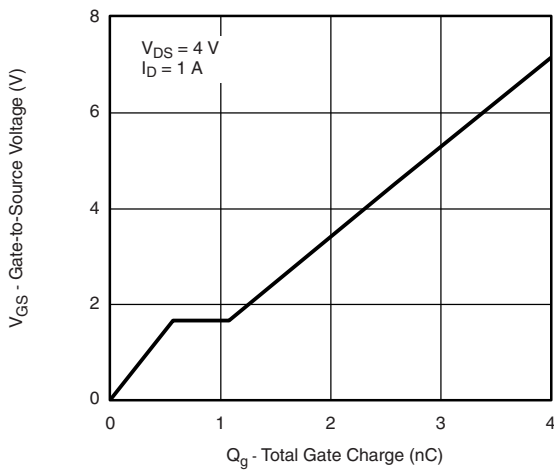
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



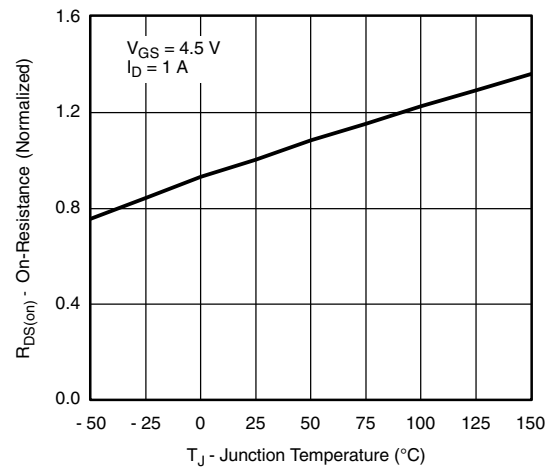
**On-Resistance vs. Drain Current**



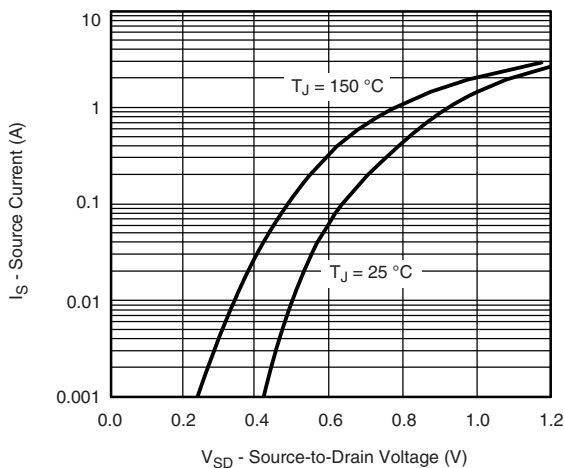
**Capacitance**



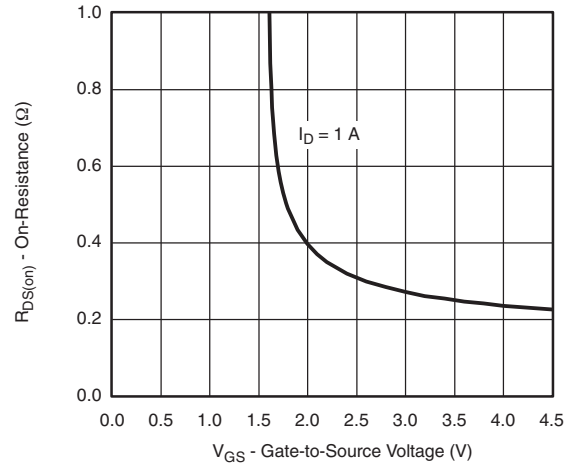
**Gate Charge**



**On-Resistance vs. Junction Temperature**

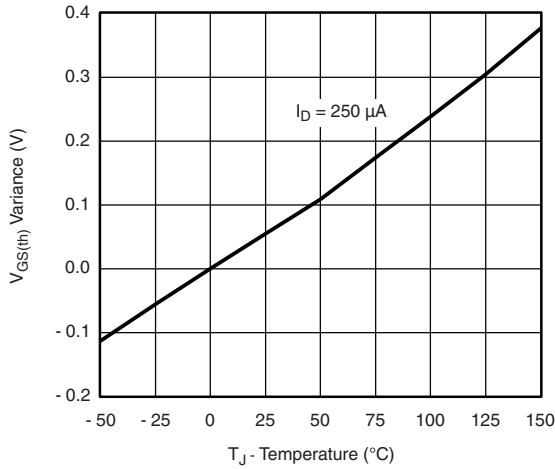


**Source-Drain Diode Forward Voltage**

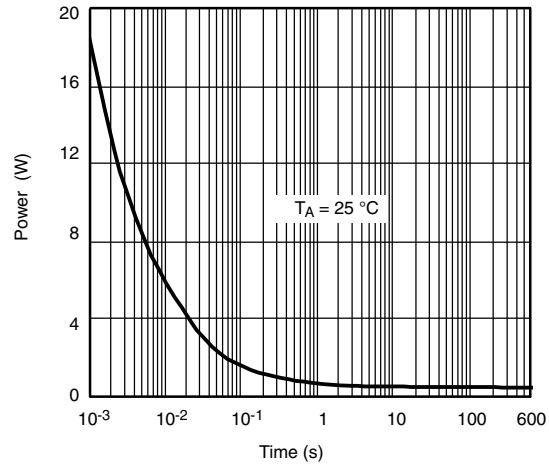


**On-Resistance vs. Gate-to-Source Voltage**

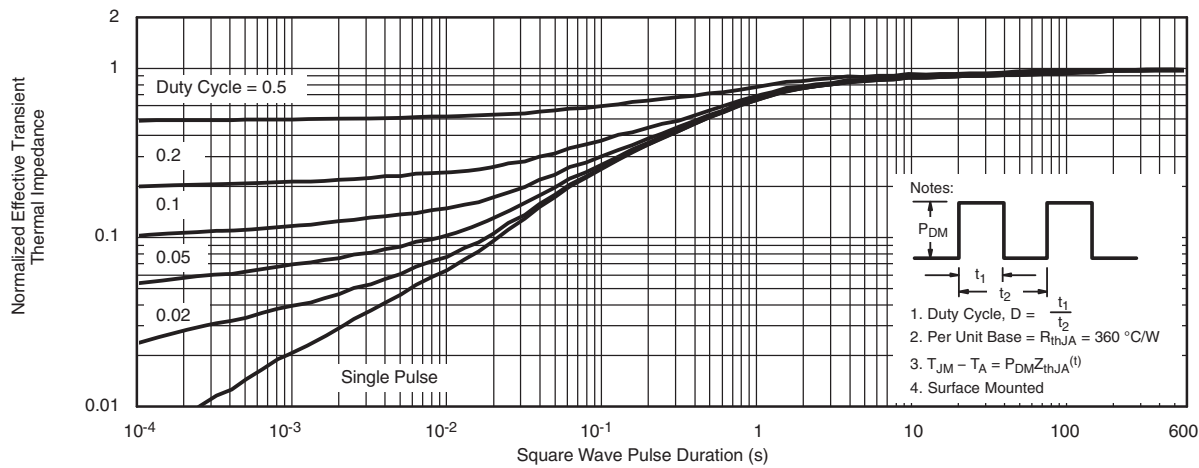
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



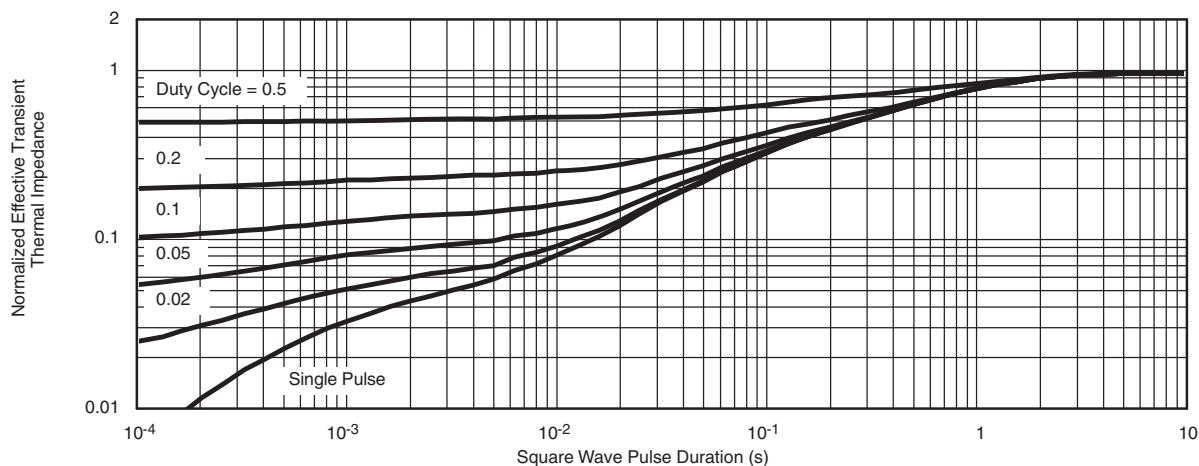
**Threshold Voltage**



**Single Pulse Power**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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